EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6233	"MOCVD" near8 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:23
L2	70	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:23
L3	0	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:23
L4	25	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:24
L5	16	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:24
L6	5	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer)) and ((support or holder) near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:25
L7	5	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer)) and ((support or holder) near8 (substrate or semiconductor or wafer)) and grow$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:27

L8	57541	(epitaxial near4 grow$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:27
L9	2471828	((epitaxial near4 grow$4) near8 semiconductor or substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:28
L10	33536	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:28
L11	1837	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:29
L12	0	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8 "MOCVD")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:29
L13	41	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:30
L14	20	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:37
L15	0	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and arsenic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:30

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L16	16	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:33
L17	15	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle and direction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:35
L18	2	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle and direction and "InP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:36
L19	11	"5494833"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:36
L20	2	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and arsenic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:38
L21	9	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and ("InGaAs" or "InAlAs")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:43
L22	19224	(semiconductor or substrate or wafer) near8 "InP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:44

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L23	5061	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:45
L24	823	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:46
L25	1	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD" and (angle near4 gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:47
L26	134	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:48
L27	97	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer)) and (crystal near4 (semiconductor or wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:48
L28	21	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer)) and (crystal near4 (semiconductor or wafer or substrate)) and (density near4 (semiconductor or wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:49
S1	16352	"MOCVD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:22

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S2	409	"MOCVD" and (polish near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:36
S3	0	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:37
S4	299	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:37
S5	7	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:37
S6	7	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient and grow$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:38
S7	2	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient and grow$4 and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:51
S8	130	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:52
S9	76	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 holder or support)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:53

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S10	39	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:53
S11	29	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:54
S12	25	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:56
S13	0	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle and gradient	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:54
S14	882909	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:56
S15	6	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:07
S16	25	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:08
S17	39	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:27

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S18	56	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:31
S19	56	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:32
S20	51	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:36
S21	17	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow$4 and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:39
S22	9	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow$4 and "InGaAs"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:41
S23	2	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow$4 and "InGaAs" and "InAlAs"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:47
S24	8	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and grow$4 and "InGaAs" and "InAlAs"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:47